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June 2012

FDMC7660

N-Channel PowerTrench $^{\! \rm I\!R}$ MOSFET 30 V, 20 A, 2.2 m Ω

Features

- Max $r_{DS(on)} = 2.2 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$, $I_D = 20 \text{ A}$
- Max $r_{DS(on)} = 3.3 \text{ m}\Omega$ at $V_{GS} = 4.5 \text{ V}$, $I_D = 18 \text{ A}$
- High performance technology for extremely low r_{DS(on)}
- Termination is Lead-free and RoHS Compliant

General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

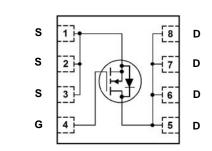
Applications

- DC DC Buck Converters
- Point of Load
- High Efficiency Load Switch and Low Side Switching



Bottom







Top

Power 33

MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			30	V
V_{GS}	Gate to Source Voltage		(Note 4)	±20	V
	Drain Current -Continuous (Package limited)	T _C = 25°C		40	
I _D	-Continuous (Silicon limited)	T _C = 25°C		100	^
	-Continuous	T _A = 25°C	(Note 1a)	20	A
	-Pulsed			200	
E _{AS}	Single Pulse Avalanche Energy		(Note 3)	200	mJ
D	Power Dissipation $T_C = 25^{\circ}C$			41	W
P_{D}	Power Dissipation	T _A = 25°C	(Note 1a)	2.3	VV
T _J , T _{STG}	Operating and Storage Junction Temperature R	ange		-55 to + 150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a	53	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC7660	FDMC7660	Power 33	13"	12 mm	3000 units

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units		
Off Chara	Off Characteristics							
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	30			V		
$\frac{\Delta BV_{DS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$, referenced to 25°C		14		mV/°C		
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μΑ		
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA		

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	1.2	1.7	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$, referenced to 25°C		-6		mV/°C
		$V_{GS} = 10 \text{ V, } I_D = 20 \text{ A}$		1.8	2.2	
r _{DS(on)}	r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 18 \text{ A}$		2.6	3.3	mΩ
	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}, T_J = 125^{\circ}\text{C}$		2.2	3.1		
g _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$		163		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 45 V V 0 V	3630	4830	pF
C _{oss}	Output Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1MHz	1345	1790	pF
C _{rss}	Reverse Transfer Capacitance	1 - 11/11/12	110	165	pF
R_g	Gate Resistance		0.9		Ω

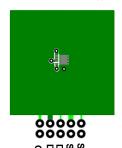
Switching Characteristics

t _{d(on)}	Turn-On Delay Time		14	25	ns
t _r	Rise Time	V _{DD} = 15 V, I _D = 20 A,	6.8	14	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	36	58	ns
t _f	Fall Time		5.7	11	ns
Qg	Total Gate Charge	V _{GS} = 0 V to 10 V	54	86	nC
Qg	Total Gate Charge	$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $V_{DD} = 15 \text{ V}$	24	38	nC
Q _{gs}	Gate to Source Charge	I _D = 20 A	11		nC
Q _{gd}	Gate to Drain "Miller" Charge		5.6		nC

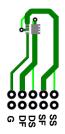
Drain-Source Diode Characteristics

Ven Source-Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 20 \text{ A}$ (Note 2)	0.8	1.2	\/	
	$V_{GS} = 0 \text{ V}, I_S = 1.9 \text{ A}$ (Note 2)	0.7	1.2] V	
t _{rr}	Reverse Recovery Time	I _E = 20 A, di/dt = 100 A/μs	45	63	ns
Q _{rr}	Reverse Recovery Charge	I _F = 20 A, α/αι = 100 A/μs	25	35	nC
Notoce					

^{1.} R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in² pad of 2 oz copper



b. 125 °C/W when mounted on a minimum pad of 2 oz copper

^{2.} Pulse Test: Pulse Width < 300 μ s, Duty cycle < 2.0%. 3. Starting $T_J = 25$ °C, L = 1 mH, $I_{AS} = 20$ A, $V_{DD} = 27$ V, $V_{GS} = 10$ V 4. As an N-channel device, the negative Vgs rating is for low duty cycle pulse ocurrence only. No continuous rating is implied.

Typical Characteristics T_J = 25°C unless otherwise noted

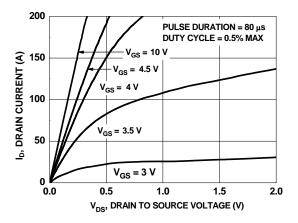


Figure 1. On Region Characteristics

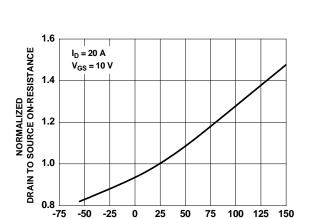


Figure 3. Normalized On Resistance vs Junction Temperature

T_J, JUNCTION TEMPERATURE (°C)

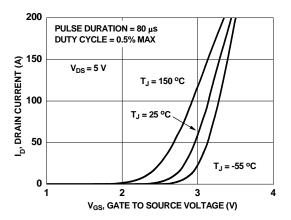


Figure 5. Transfer Characteristics

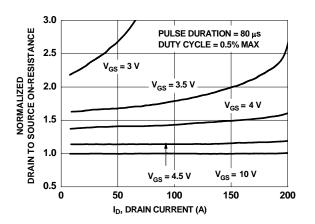


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

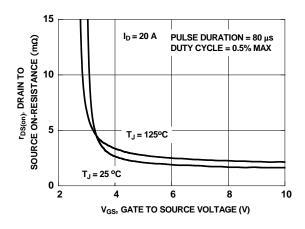


Figure 4. On-Resistance vs Gate to Source Voltage

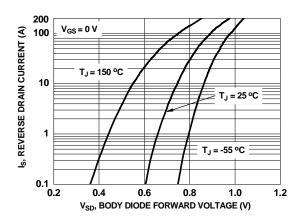


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

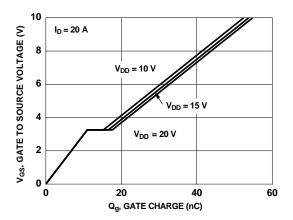


Figure 7. Gate Charge Characteristics

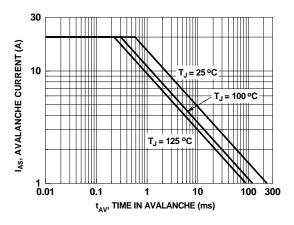


Figure 9. Unclamped Inductive Switching Capability

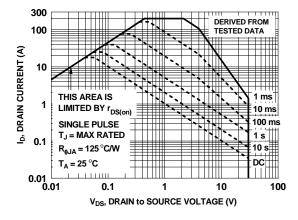


Figure 11. Forward Bias Safe Operating Area

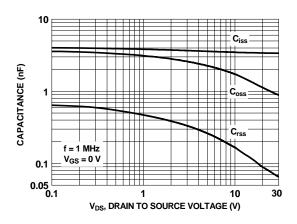


Figure 8. Capacitance vs Drain to Source Voltage

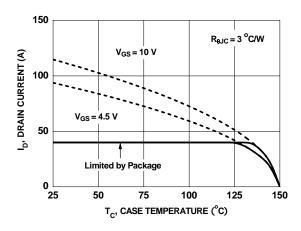


Figure 10. Maximum Continuous Drain Current vs Case Temperature

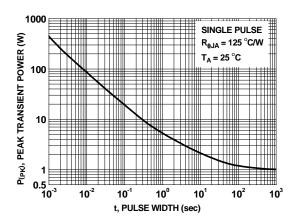


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

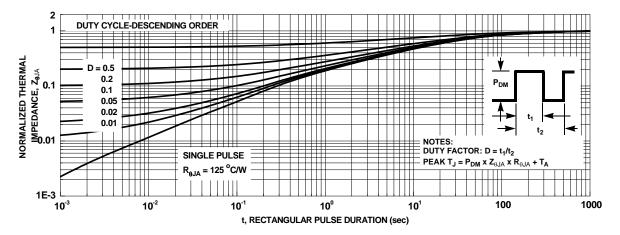
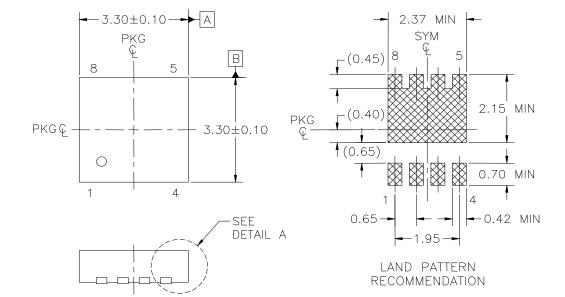
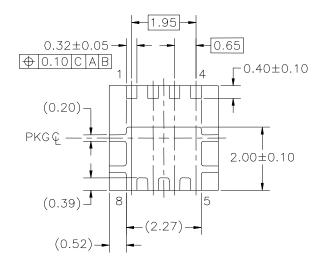
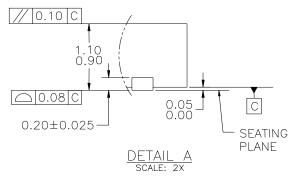


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout







PQFN08BREV1

NOTES: UNLESS OTHERWISE SPECIFIED

- PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. BA, DATED OCTOBER 2002.
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 BURRS DOES NOT EXCEED 0.10MM. C)
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